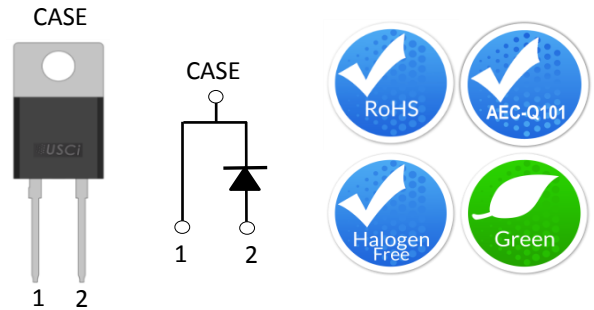


## Description

United Silicon Carbide, Inc. offers the 3<sup>rd</sup> generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D1202TS	TO-220-2L	UJ3D1202TS

## Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified

## Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

## Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	$V_R$		1200	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	$V_{RRM}$		1200	V
Surge peak reverse voltage	$V_{RSM}$		1200	V
Maximum DC forward current	$I_F$	$T_C = 164^\circ\text{C}$	2	A
Non-repetitive forward surge current sine halfwave	$I_{FSM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	30	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	27	
Repetitive forward surge current sine halfwave, $D=0.1$	$I_{FRM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	14.8	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	8.8	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	250	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	250	
$i^2t$ value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	4.5	$\text{A}^2\text{s}$
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	3.6	
Power dissipation	$P_{Tot}$	$T_C = 25^\circ\text{C}$	75	W
		$T_C = 164^\circ\text{C}$	5.5	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	$T_J, T_{STG}$		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	$T_{sold}$	1.6mm from case for 10s	260	$^\circ\text{C}$

**Electrical Characteristics**

$T_J = +25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	$V_F$	$I_F=2\text{A}, T_J=25^\circ\text{C}$	-	1.4	1.6	V
		$I_F=2\text{A}, T_J=150^\circ\text{C}$	-	1.85	2.3	
		$I_F=2\text{A}, T_J=175^\circ\text{C}$	-	2	2.6	
Reverse current	$I_R$	$V_R=1200\text{V}, T_J=25^\circ\text{C}$	-	20	95	$\mu\text{A}$
		$V_R=1200\text{V}, T_J=175^\circ\text{C}$	-	200		
Total capacitive charge <sup>(1)</sup>	$Q_C$	$V_R=800\text{V}$		12		nC
Total capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$		109		pF
		$V_R=400\text{V}, f=1\text{MHz}$		11.5		
		$V_R=800\text{V}, f=1\text{MHz}$		9.8		
Capacitance stored energy	$E_C$	$V_R=800\text{V}$		3.6		$\mu\text{J}$

(1)  $Q_C$  is independent on  $T_J$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.

**Thermal characteristics**

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			1.5	2	$^\circ\text{C}/\text{W}$

**Typical Performance**

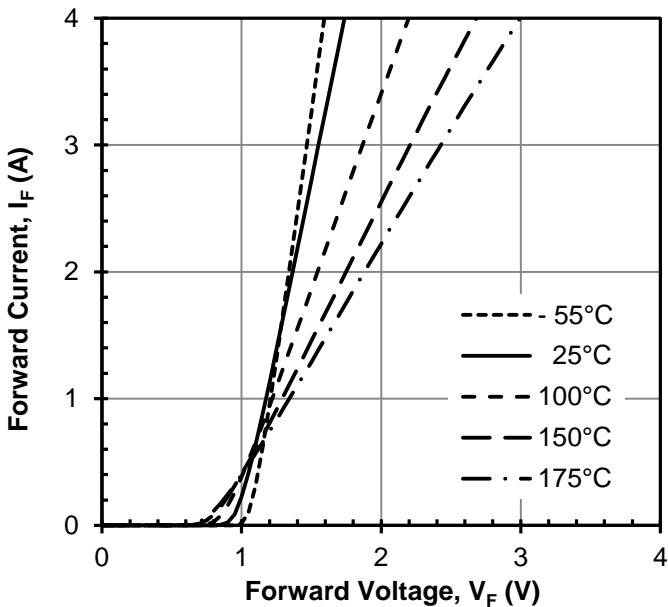


Figure 1 Typical forward characteristics

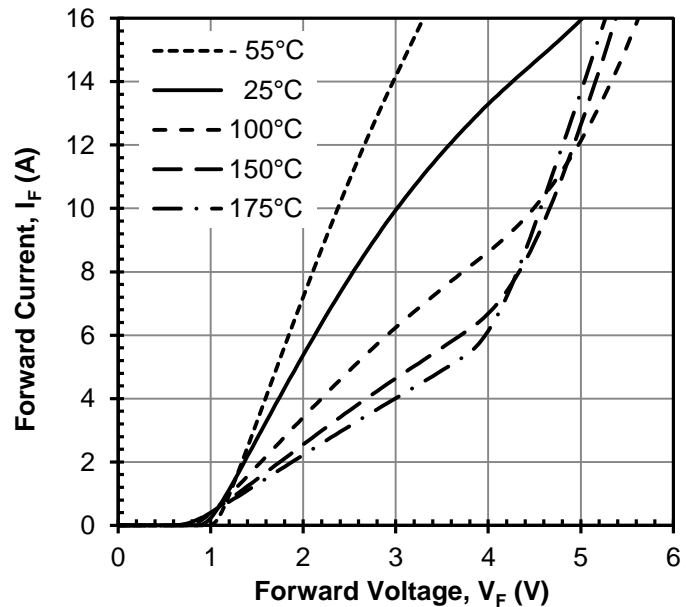


Figure 2 Typical forward characteristics in surge current

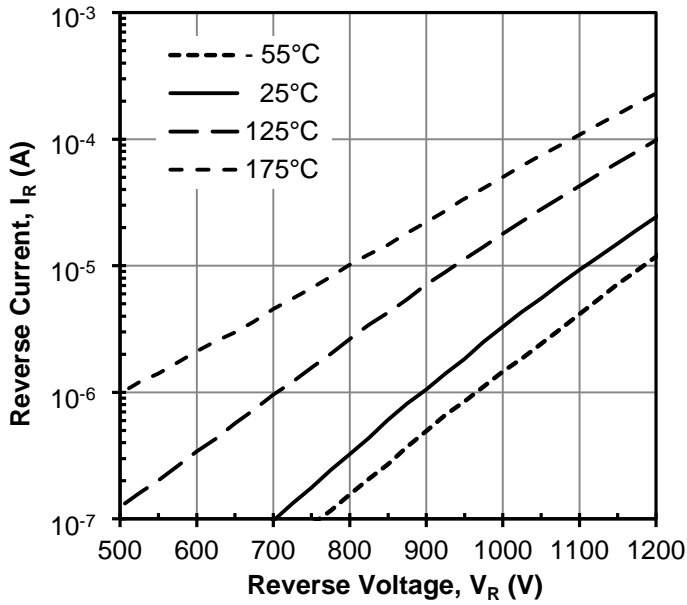


Figure 3 Typical reverse characteristics

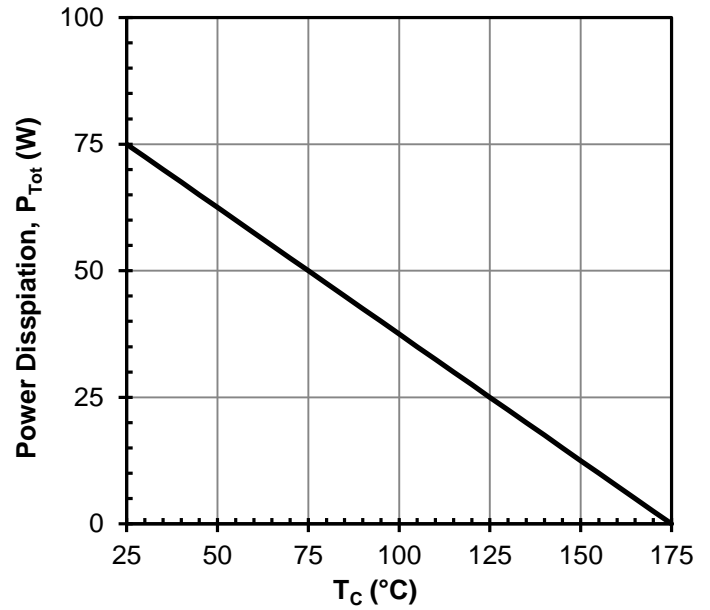


Figure 4 Power dissipation

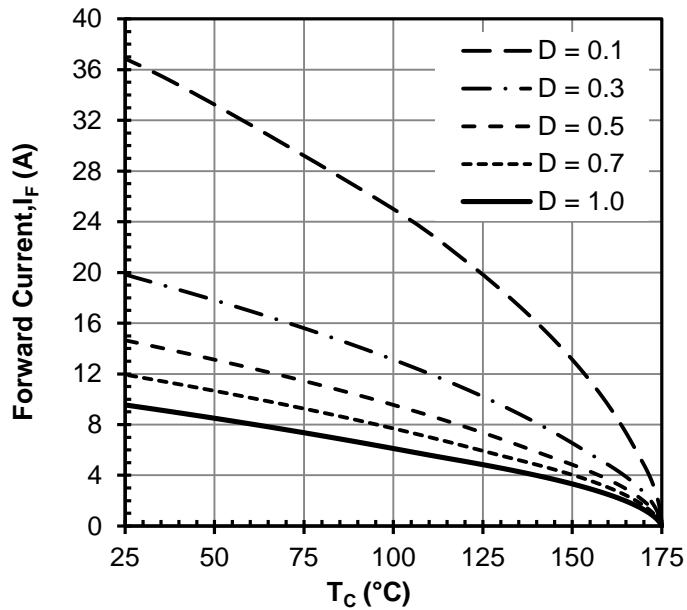


Figure 5 Diode forward current

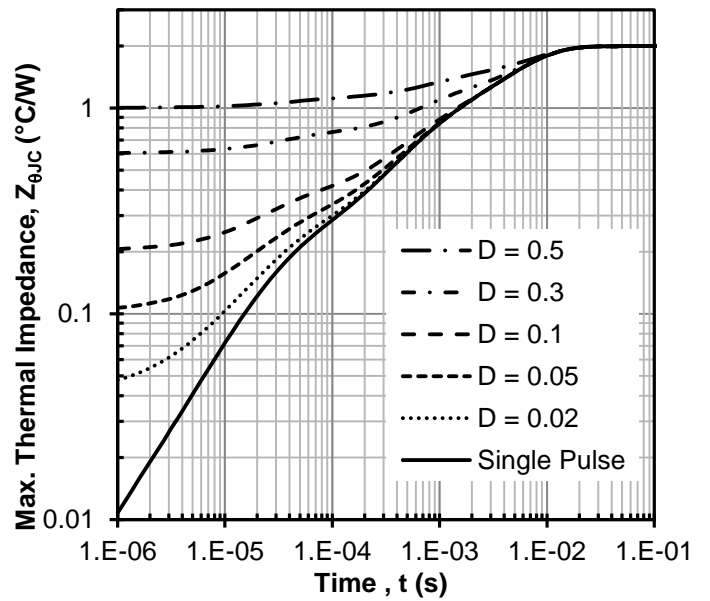


Figure 6 Maximum transient thermal impedance

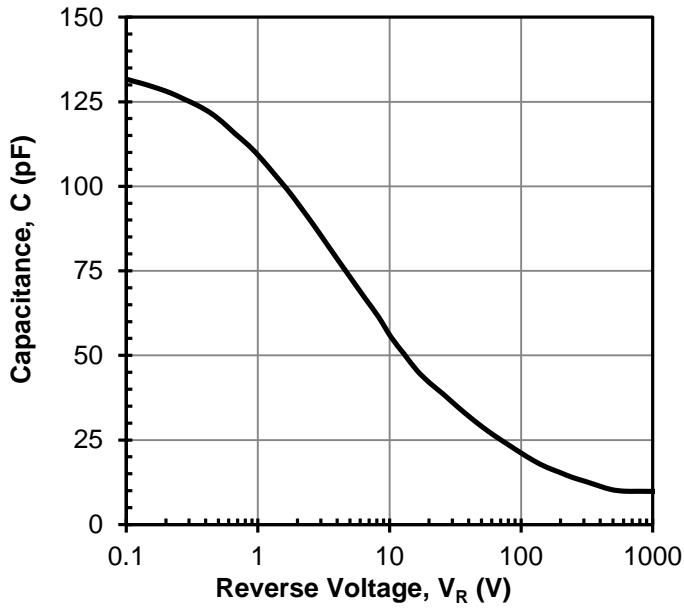


Figure 7 Capacitance vs. reverse voltage at 1MHz

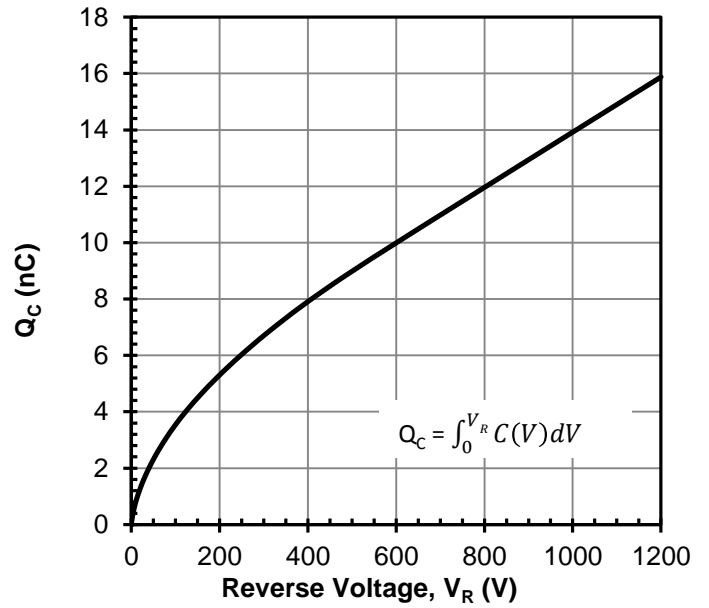


Figure 8 Typical capacitive charge vs. reverse voltage

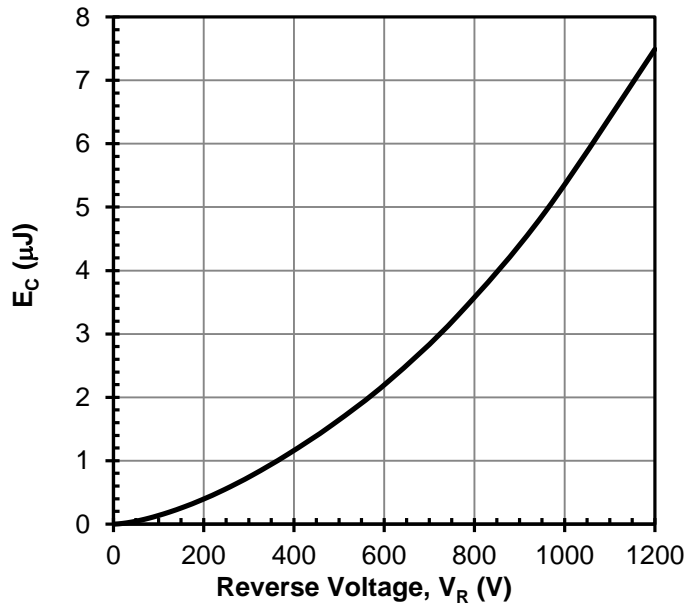


Figure 9 Typical capacitance stored energy vs. reverse voltage

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